

AMENDMENTS TO THE CLAIMS

Please cancel Claims 4, 6 and 24.

Please amend Claim 1, 5, 7-9, 13, 15, 23, 27 and 28 as indicated below.

1. (Currently Amended for the Third Time) A process of forming a gate structure on a semiconductor substrate, comprising:

E1 providing a semiconductor substrate having a channel region formed therein so as to define a source and a drain region and a gate structure comprised of a gate dielectric positioned on said channel region and a conductive layer positioned on said gate dielectric; implanting ~~an insulator element region~~ nitrogen into said substrate; and ~~transforming a portion of said conductive layer adjacent said insulator element region into~~ conducting a source/drain reoxidation, thereby forming a sidewall spacer after forming the insulator element region implanting said nitrogen.

2. (Previously Canceled)

E2 3. (Previously Amended) The process of Claim 1, wherein said substrate comprises silicon.

4. (Currently Canceled)

E3 5. (Currently Amended) The process of Claim ~~A~~ 1, wherein ~~forming said insulator element region~~ implanting said nitrogen comprises doping the substrate with greater than about 10^{12} nitrogen atoms.

6. (Currently Canceled)

E4 7. (Currently Amended) The process of Claim ~~6~~ 1, wherein said conductive layer comprises polysilicon.

8. (Currently Amended) The process of Claim ~~6~~ 1, wherein ~~oxidizing said portion further~~ conducting said source/drain reoxidation comprises growing a bird's beak region extending laterally into a selected portion of said conductive layer.

9. (Currently Amended) The process of Claim ~~6~~ 1, wherein ~~oxidizing said portion further~~ conducting said source/drain reoxidation comprises forming a nitride layer on said semiconductor substrate.

10. (Original) The process of Claim 9, wherein said nitride layer laterally extends under at least a portion of said conductive layer.